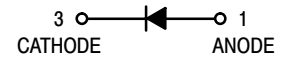
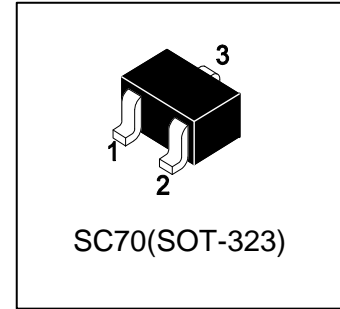


# LBAS16WT1G

## S-LBAS16WT1G

Silicon Switching Diode



### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

### 2. DEVICE MARKING AND RESISTOR VALUES

| Device     | Marking | Shipping        |
|------------|---------|-----------------|
| LBAS16WT1G | A6      | 3000/Tape&Reel  |
| LBAS16WT3G | A6      | 10000/Tape&Reel |

### 3. MAXIMUM RATINGS(Ta = 25°C)

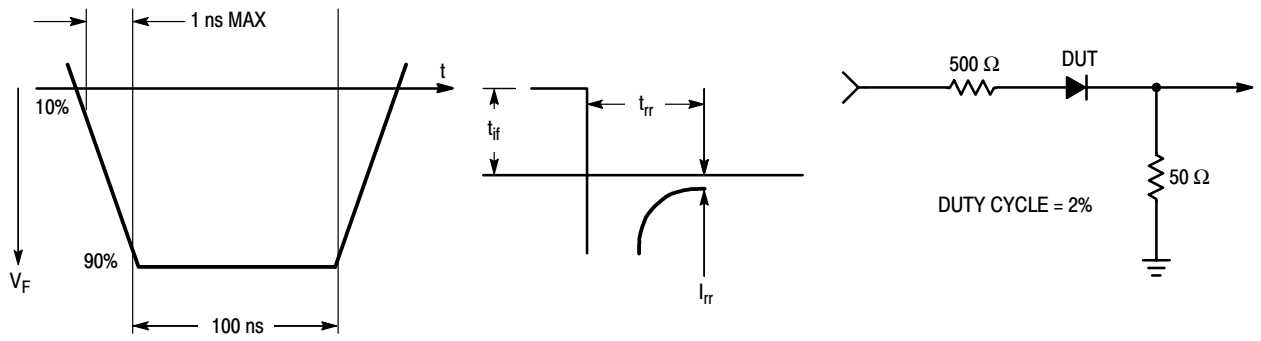
| Parameter  | Symbol | Limits | Unit |
|--|--------|--------|------|
| Continuous Reverse Voltage                       | VR     | 75     | V    |
| Peak Forward Current                             | IR     | 200    | mA   |
| Peak Forward Surge Current (Pulse Width = 10 μs) | IFSM   | 500    | mA   |

### 4. THERMAL CHARACTERISTICS

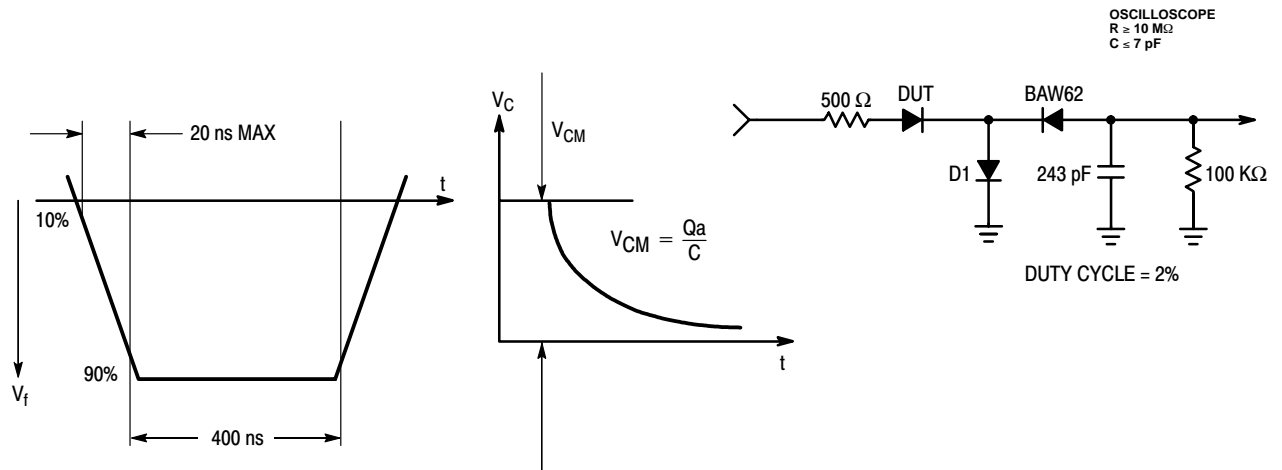
| Parameter  | Symbol    | Limits     | Unit        |
|--|-----------|------------|-------------|
| Total Power Dissipation, One Diode Loaded<br>TA = 25°C<br>Derate above 25°C<br>Mounted on a Ceramic Substrate(10 x 8 x 0.6 mm) | PD        | 200<br>1.6 | mW<br>mW/°C |
| Thermal Resistance, Junction to Ambient<br>One Diode Loaded<br>Mounted on a Ceramic Substrate(10 x 8 x 0.6 mm)                 | RθJA      | 0.625      | °C/mW       |
| Junction and Storage Temperature   | TJ , Tstg | -55~+150   | °C          |

**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

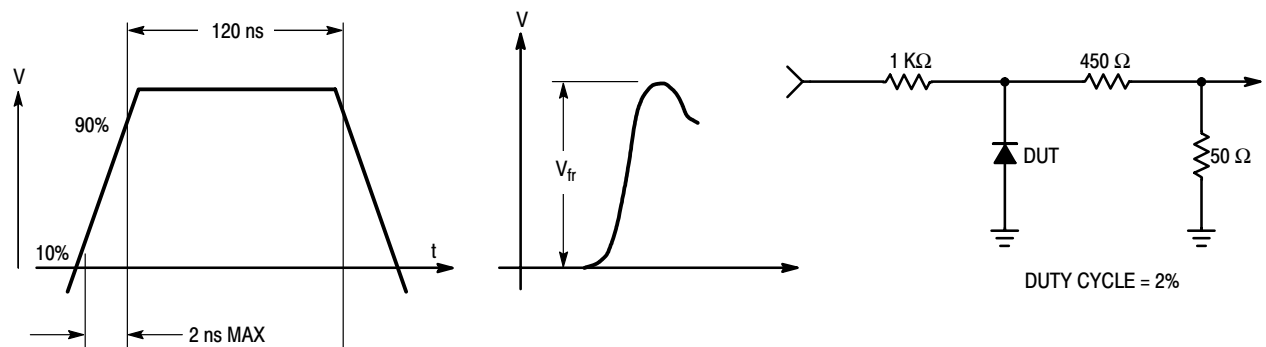
| CHARACTERISTICS  | Symbol | Min | Max  | Unit |
|--|--------|-----|------|------|
| Forward voltage<br>(IF =1mA)                                     | VF     | -   | 715  | mV   |
| (IF =10mA)   |        | -   | 855  |      |
| (IF =50mA)   |        | -   | 1000 |      |
| (IF =150mA)  |        | -   | 1250 |      |
| Reverse Current<br>(VR=75V)                                      | IR     | -   | 1    | μA   |
| (VR=75V, TJ = 150°C)   |        | -   | 50   |      |
| (VR=25V, TJ = 150°C)   |        | -   | 30   |      |
| Diode capacitance<br>(f=1MHz,VR =0)                              | Cd     | -   | 2    | pF   |
| Reverse Recovery Time (Figure 1)<br>(IF = IR = 10mA, RL = 50Ω)   | Trr    | -   | 6    | nS   |
| Stored Charge (Figure 2)<br>(IF = 10 mA to VR = 6.0V, RL = 500Ω) | QS     | -   | 45   | pC   |
| Forward Recovery Voltage (Figure 3)<br>(IF = 10 mA, tr = 20ns)   | VFR    | -   | 1.75 | V    |



**Figure 1. Reverse Recovery Time Equivalent Test Circuit**

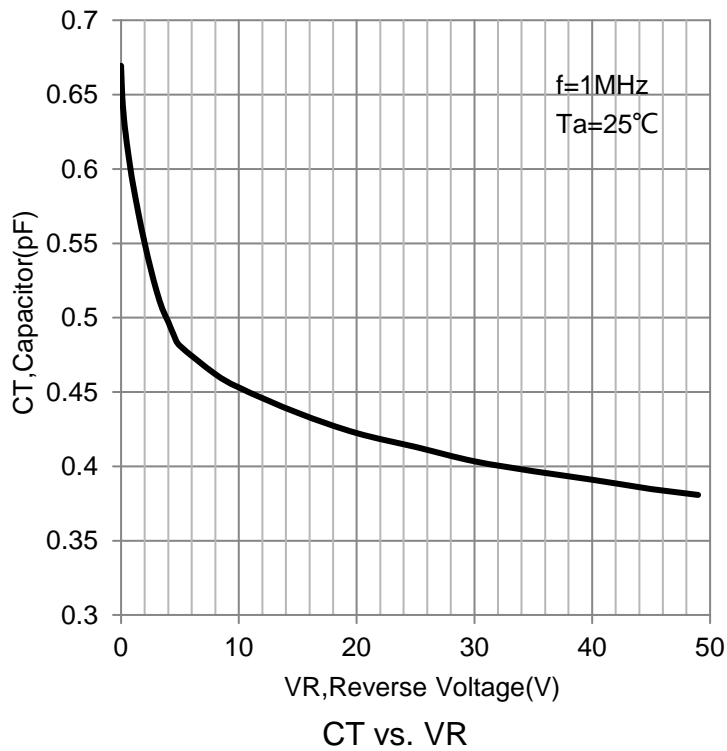
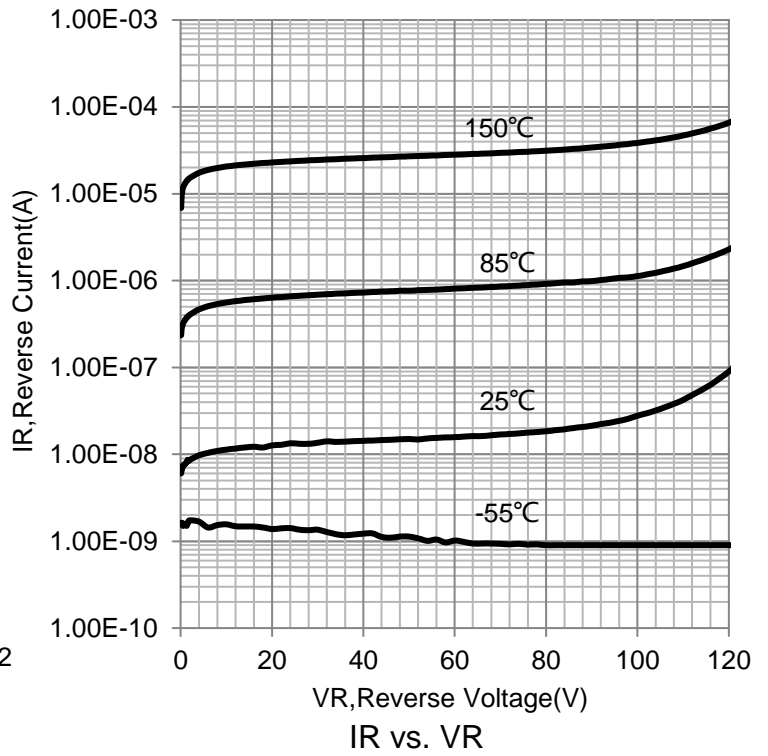
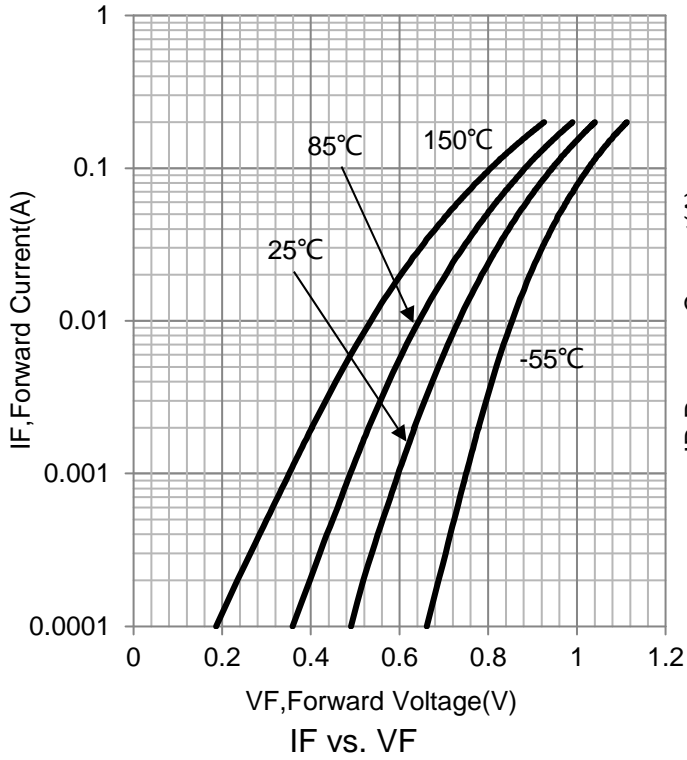


**Figure 2. Recovery Charge Equivalent Test Circuit**

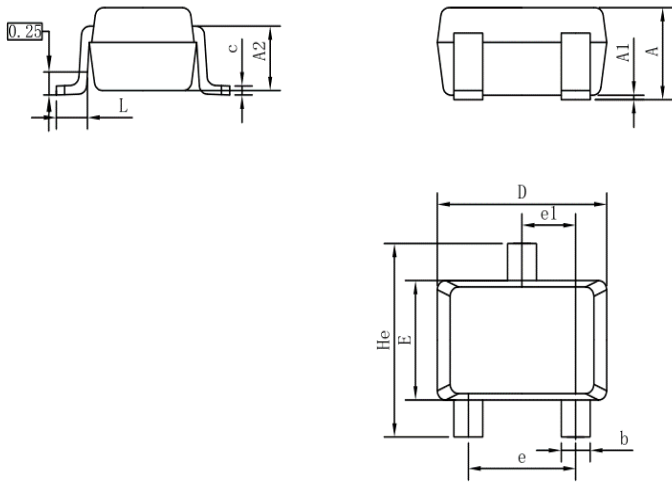


**Figure 3. Forward Recovery Voltage Equivalent Test Circuit**

**6.ELECTRICAL CHARACTERISTICS CURVES**

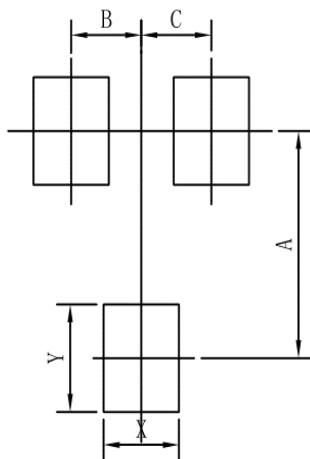


### 7. OUTLINE AND DIMENSIONS



| SC70                |          |      |      |
|---------------------|----------|------|------|
| DIM                 | MIN      | NOR  | MAX  |
| A                   | 0.80     | 0.95 | 1.00 |
| A1                  | 0.00     | 0.05 | 0.10 |
| A2                  | 0.7 REF  |      |      |
| b                   | 0.30     | 0.35 | 0.40 |
| c                   | 0.10     | 0.15 | 0.25 |
| D                   | 1.80     | 2.05 | 2.20 |
| E                   | 1.15     | 1.30 | 1.35 |
| e                   | 1.20     | 1.30 | 1.40 |
| e1                  | 0.65 BSC |      |      |
| L                   | 0.20     | 0.35 | 0.56 |
| He                  | 2.00     | 2.10 | 2.40 |
| ALL Dimension in mm |          |      |      |

### 8. SOLDERING FOOTPRINT



| SC70 |      |
|------|------|
| DIM  | MIN  |
| A    | 1.90 |
| B    | 0.65 |
| C    | 0.65 |
| X    | 0.70 |
| Y    | 0.90 |

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)